

Johan Rothman

List of Publications by Year in descending order

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45
papers

970
citations

430874

18
h-index

454955

30
g-index

46
all docs

46
docs citations

46
times ranked

669
citing authors

#	ARTICLE	IF	CITATIONS
1	Meso-photonic Detection with HgCdTe APDs at High Count Rates. Journal of Electronic Materials, 2020, 49, 6881-6892.	2.2	8
2	Performances of a HGCDTE APD based direct detection lidar at 2 $\hat{1}$ / ₄ m. Application to dial measurements. EPJ Web of Conferences, 2018, 176, 01001.	0.3	4
3	Physics and Limitations of HgCdTe APDs: A Review. Journal of Electronic Materials, 2018, 47, 5657-5665.	2.2	31
4	Shockleyâ€“Readâ€“Hall Lifetime Study and Implication in HgCdTe Photodiodes for IR Detection. Journal of Electronic Materials, 2018, 47, 5680-5690.	2.2	12
5	HgCdTe APDs for free space optical communications. , 2018, , .		1
6	HgCdTe APDs for low-photon number IR detection. Proceedings of SPIE, 2017, , .	0.8	1
7	Optically pumped GeSn micro-disks with 16% Sn lasing at 3.1 $\hat{1}$ / ₄ m up to 180â€‰K. Applied Physics Letters, 2017, 111, .	3.3	156
8	Temperature and Injection Dependence of Photoluminescence Decay in Midwave Infrared HgCdTe. Journal of Electronic Materials, 2017, 46, 6817-6828.	2.2	8
9	HgCdTe APDs for time-resolved space applications. CEAS Space Journal, 2017, 9, 507-516.	2.3	9
10	Evaluation of a HgCdTe e-APD based detector for 2â€‰ $\hat{1}$ / ₄ m CO ₂ DIAL application. Applied Optics, 2017, 56, 7577.	1.8	22
11	Gamma bandgap determination in pseudomorphic GeSn layers grown on Ge with up to 15% Sn content. Applied Physics Letters, 2016, 109, .	3.3	30
12	Latest achievements on MCT IR detectors for space and science imaging. Proceedings of SPIE, 2016, , .	0.8	2
13	HgCdTe Detectors for Space and Science Imaging: General Issues and Latest Achievements. Journal of Electronic Materials, 2016, 45, 4532-4541.	2.2	46
14	MCT APD focal plane arrays for astronomy at CEA-LETI. , 2016, , .		3
15	HgCdTe APDs for free space optical communications. Proceedings of SPIE, 2015, , .	0.8	8
16	Characterization of midwave infrared InSb avalanche photodiode. Journal of Applied Physics, 2015, 117, .	2.5	29
17	Response Time Measurements in Short-Wave Infrared HgCdTe e-APDs. Journal of Electronic Materials, 2014, 43, 2947-2954.	2.2	20
18	Characterization of Plasma Etching Process Damage in HgCdTe. Journal of Electronic Materials, 2013, 42, 3006-3014.	2.2	9

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19	Modeling of Dark Current in HgCdTe Infrared Detectors. Journal of Electronic Materials, 2013, 42, 3303-3308.	2.2	20
20	Electrical modeling of InSb PiN photodiode for avalanche operation. Journal of Applied Physics, 2013, 113, .	2.5	28
21	Issues in HgCdTe Research and Expected Progress in Infrared Detector Fabrication. Journal of Electronic Materials, 2013, 42, 3349-3358.	2.2	30
22	A novel 0.5GHz real time asynchronous photon detection and counting technique: ROIC design for cooled SWIR HgCdTe infrared detector. , 2013, , .		0
23	Design, fabrication, and characterization of InSb avalanche photodiode. Proceedings of SPIE, 2013, , .	0.8	0
24	Short-Wave Infrared HgCdTe Avalanche Photodiodes. Journal of Electronic Materials, 2012, 41, 2928-2936.	2.2	104
25	Performance of Mid-Wave Infrared HgCdTe e-Avalanche Photodiodes. Journal of Electronic Materials, 2012, 41, 2943-2948.	2.2	28
26	Small pixel pitch solutions for active and passive imaging. Proceedings of SPIE, 2012, , .	0.8	0
27	Linear photon-counting with HgCdTe APDs. , 2012, , .		13
28	A 320x256 HgCdTe avalanche photodiode focal plane array for passive and active 2D and 3D imaging. , 2011, , .		9
29	History-Dependent Impact Ionization Theory Applied to HgCdTe e-APDs. Journal of Electronic Materials, 2011, 40, 1757-1768.	2.2	37
30	HgCdTe Quantum Detection: from Long-Wave IR down to UV. Journal of Electronic Materials, 2011, 40, 1781-1784.	2.2	10
31	Shockleyâ€“Haynes Characterization of Minority-Carrier Drift Velocity, Diffusion Coefficient, and Lifetime in HgCdTe Avalanche Photodiodes. Journal of Electronic Materials, 2010, 39, 837-845.	2.2	3
32	HgCdTe APD-focal plane array development at DEFIR. Proceedings of SPIE, 2010, , .	0.8	10
33	Sub electron readout noise & photon counting devices. EAS Publications Series, 2009, 37, 255-270.	0.3	2
34	A Monte Carlo Study of $\text{Hg}_{0.7}\text{Cd}_{0.3}\text{Te}$ e-APD. IEEE Transactions on Electron Devices, 2009, 56, 569-577.	3.0	25
35	Study of the Transit-Time Limitations of the Impulse Response in Mid-Wave Infrared HgCdTe Avalanche Photodiodes. Journal of Electronic Materials, 2009, 38, 1790-1799.	2.2	44
36	High-Operating-Temperature HgCdTe Avalanche Photodiodes. Journal of Electronic Materials, 2009, 38, 1707-1716.	2.2	13

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37	Experimental Performance and Monte Carlo Modeling of Long Wavelength Infrared Mercury Cadmium Telluride Avalanche Photodiodes. Journal of Electronic Materials, 2009, 38, 1628-1636.	2.2	12
38	HgCdTe APD-focal plane array performance at DEFIR. Proceedings of SPIE, 2009, , .	0.8	8
39	New high-gain detectors for active imaging. , 2009, , .		3
40	Latest Developments of HgCdTe e-APDs at CEA LETI-Minatec. Journal of Electronic Materials, 2008, 37, 1303-1310.	2.2	31
41	Impulse Response Time Measurements in Hg _{0.7} Cd _{0.3} Te MWIR Avalanche Photodiodes. Journal of Electronic Materials, 2008, 37, 1261-1273.	2.2	41
42	HgCdTe APD- focal plane array development at CEA Leti-Minatec. Proceedings of SPIE, 2008, , .	0.8	10
43	A Monte Carlo study of multiplication and noise in HgCdTe avalanche photodiodes. , 2008, , .		3
44	High performance characteristics in pin MW HgCdTe e-APDs. , 2007, , .		24
45	Gain and Dark Current Characteristics of Planar HgCdTe Avalanche Photo Diodes. Journal of Electronic Materials, 2007, 36, 963-970.	2.2	63